

NDT014L

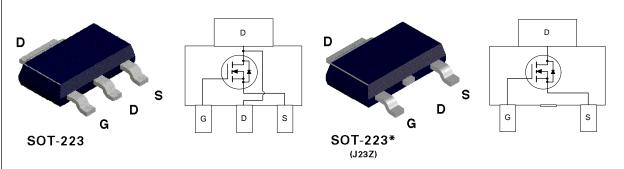
N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

These N-Channel logic level enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- = 2.8 A, 60 V. $R_{\rm DS(ON)} = 0.2~\Omega$ @ $V_{\rm GS} = 4.5~{\rm V}$ $R_{\rm DS(ON)} = 0.16~\Omega$ @ $V_{\rm GS} = 10~{\rm V}$.
- High density cell design for extremely low R_{DS(ON)}.
- High power and current handling capability in a widely used surface mount package.



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		NDT014L	Units
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		± 20	V
I _D	Drain Current - Continuous	(Note 1a)	± 2.8	A
	- Pulsed		± 10	
P _D	Maximum Power Dissipation	(Note 1a)	3	W
		(Note 1b)	1.3	
		(Note 1c)	1.1	
T_J, T_{STG}	Operating and Storage Temperature F	Range	-65 to 150	°C
THERMA	L CHARACTERISTICS			_
R _{eJA}	Thermal Resistance, Junction-to-Amb	pient (Note 1a)	42	°C/W
R _{ØJC}	Thermal Resistance, Junction-to-Case	e (Note 1)	12	°C/W

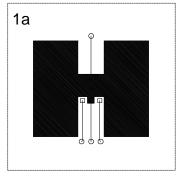
Symbol	Parameter	Conditions	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS					•	•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$				V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	V _{DS} = 60 V, V _{GS} = 0 V				
			$T_J = 55^{\circ}C$			250	μΑ
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHAR	ACTERISTICS (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		1	1.5	3	V
			T _J = 125°C	8.0	1.1	2	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 4.5 \text{ V}, I_{D} = 2.8 \text{ A}$			0.17	0.2	Ω
			T _J = 125°C		0.22	0.36	
		$V_{GS} = 10 \text{ V}, I_{D} = 3.4 \text{ A}$	$V_{GS} = 10 \text{ V}, I_D = 3.4 \text{ A}$				
I _{D(on)}	On-State Drain Current		5			Α	
		$V_{GS} = 10 \text{ V}, V_{DS} = 5 \text{ V}$	10				
G _{FS}	Forward Transconductance	$V_{GS} = 5 \text{ V}, I_{D} = 2.8 \text{ A}$		4.2		S	
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V},$			214		pF
C _{oss}	Output Capacitance	f = 1.0 MHz			70		pF
C _{rss}	Reverse Transfer Capacitance		7				pF
SWITCHIN	NG CHARACTERISTICS (Note 2)						
$\mathbf{t}_{D(on)}$	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 3 \text{ A},$			6	12	ns
t,	Turn - On Rise Time	V_{GEN} = 10 V, R_{GEN} = 12 Ω			14	25	ns
$\mathbf{t}_{D(off)}$	Turn - Off Delay Time			15	28	ns	
t,	Turn - Off Fall Time				10	18	ns
Q_g	Total Gate Charge	$V_{DS} = 10 \text{ V},$			3.6	5	nC
Q_{gs}	Gate-Source Charge	$I_D = 2.8 \text{ A}, V_{GS} = 4.5 \text{ V}$			0.8		nC
Q_{gd}	Gate-Drain Charge				1.4		nC

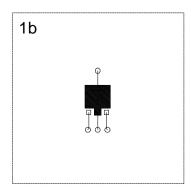
Electrical Characteristics (T _A = 25°C unless otherwise noted)									
Symbol	Parameter Conditions Min Typ Max U								
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS									
Is	Maximum Continuous Drain-Source Diode Forward Current 2.3								
V _{SD}	Drain-Source Diode Forward Voltage		0.85	1.3	V				
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_F = 2.3 \text{ A } dI_F/dt = 100 \text{ A/}\mu\text{s}$			140	ns			

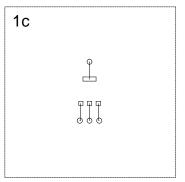
Notes:

- Notes:
 1. $P_D(t) = \frac{T_J T_A}{R_{BJA}(t)} = \frac{T_J T_A}{R_{BJC} + R_{BCA}(t)} = I_D^2(t) \times R_{DS(ON) \oplus T_J} R_{\text{Bu}A}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\text{Bu}S}$ is guaranteed by design while R_{BCA} is defined by users. For general reference: Applications on 4.5"x5" FR-4 PCB under still air environment, typical R_{BA} is found to be:

 a. 42"C/W with 1 in² of 2 oz copper mounting pad.
 b. 95"C/W with 0.066 in² of 2 oz copper mounting pad.
 c. 110"C/W with 0.0123 in² of 2 oz copper mounting pad.







Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

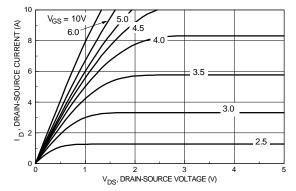


Figure 1. On-Region Characteristics.

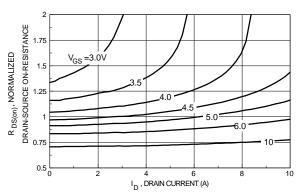


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

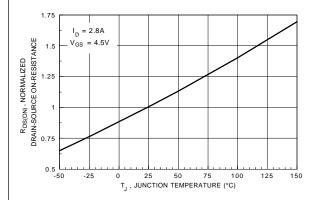


Figure 3. On-Resistance Variation with Temperature.

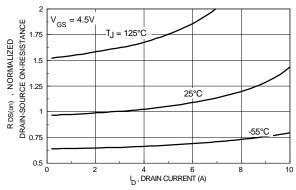


Figure 4. On-Resistance Variation with Drain Current and Temperature.

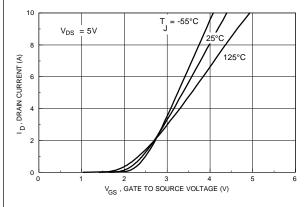


Figure 5. Transfer Characteristics.

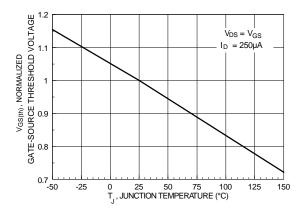


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics

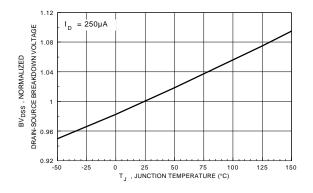


Figure 7. Breakdown Voltage Variation with Temperature.

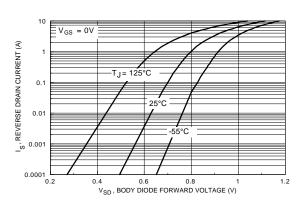


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

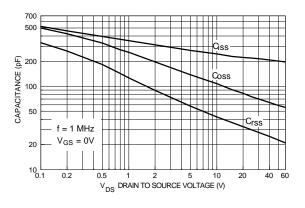


Figure 9. Capacitance Characteristics.

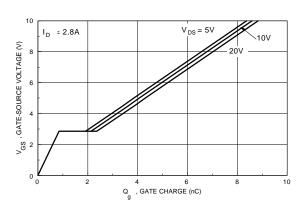


Figure 10. Gate Charge Characteristics.

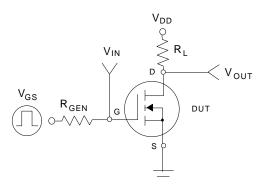


Figure 11. Switching Test Circuit.

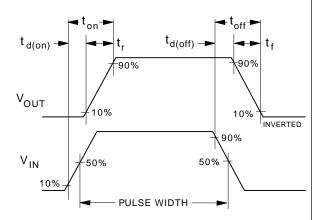
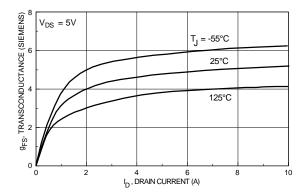


Figure 12. Switching Waveforms.

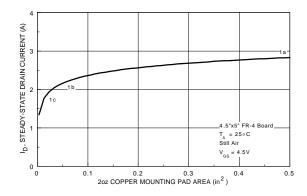
Typical Thermal Characteristics



3.5 STEADY-STATE POWER DISSIPATION (W) 3 T_A = 25° C Still Air 0.4 0.8 20z COPPER MOUNTING PAD AREA (in ²)

Figure 13. Transconductance Variation with Drain **Current and Temperature.**

Figure 14. SOT-223 Maximum Steady- State **Power Dissipation versus Copper** Mounting Pad Area.



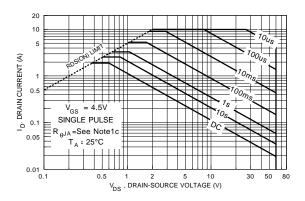


Figure 15. Maximum Steady- State Drain **Current versus Copper Mounting Pad** Area.

Figure 16. Maximum Safe Operating Area.

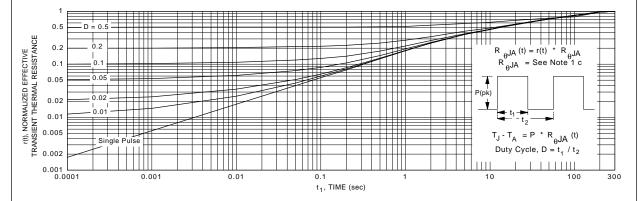
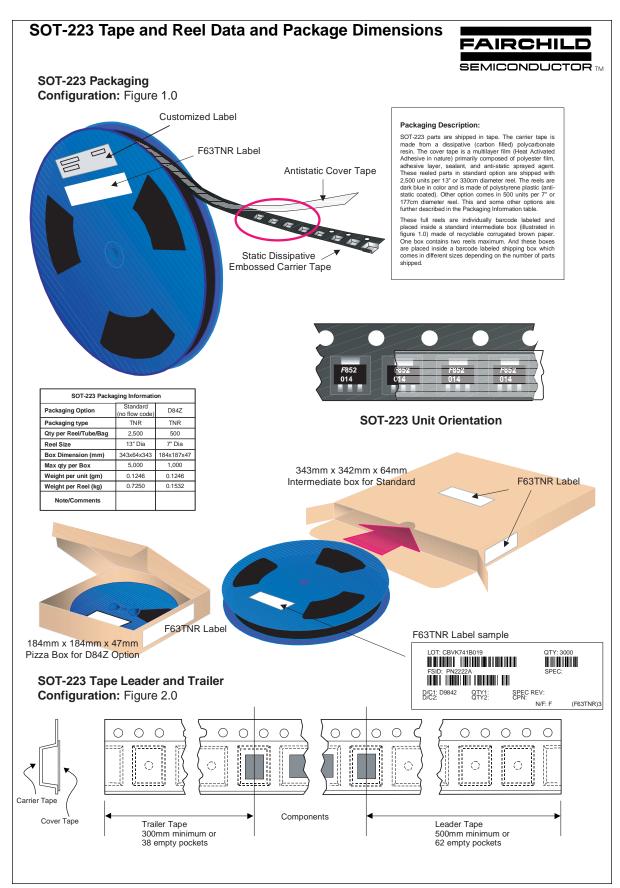


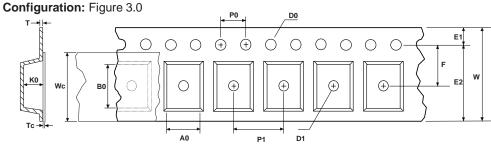
Figure 17. Typical Transient Thermal Impedance Curve.

Remark: Thermal characterization performed under the conditions of Note 1c. Should better thermal design employs, R_{eux} will be lower and reach thermal equivalent sooner.





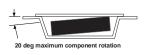
SOT-223 Embossed Carrier Tape



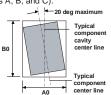
User Direction of Feed	
	$\overline{}$

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

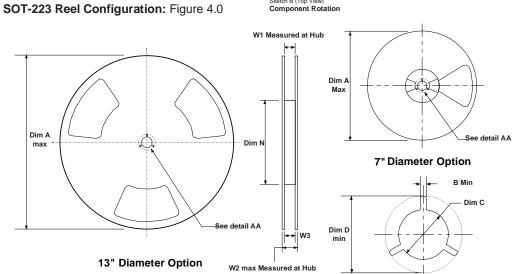


Sketch B (Top View)
Component Rotation

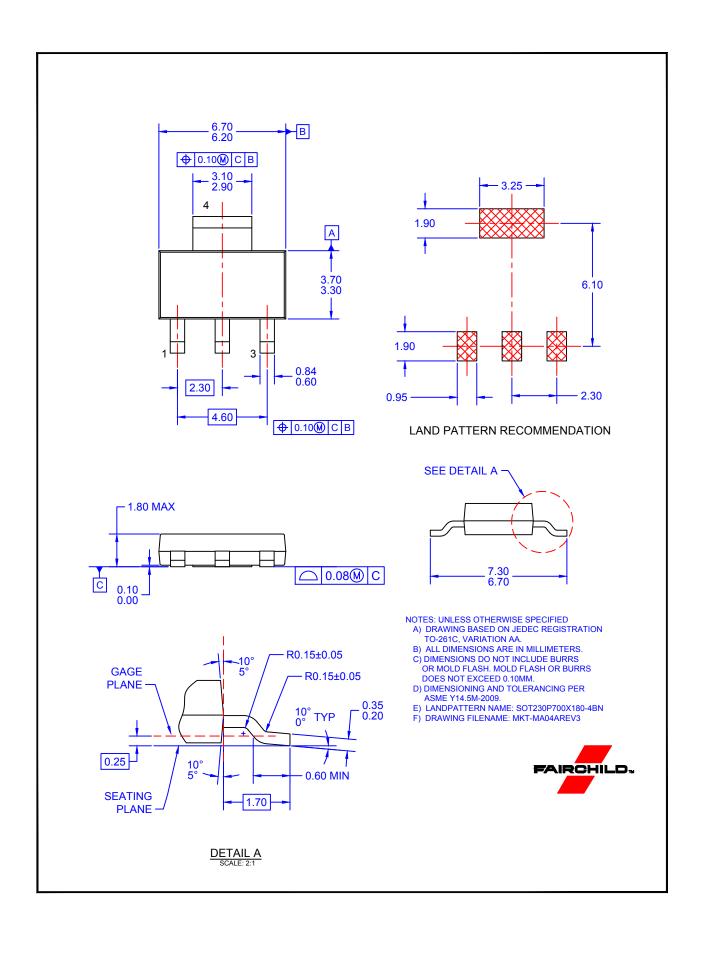


Sketch C (Top View)
Component lateral movement

DETAIL AA



	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4







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Datasheet Identification		Definition
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